

## N-channel 600 V, 0.06 $\Omega$ typ., 42 A MDmesh™ M2 Power MOSFET in a TO247-4 package

Datasheet - production data

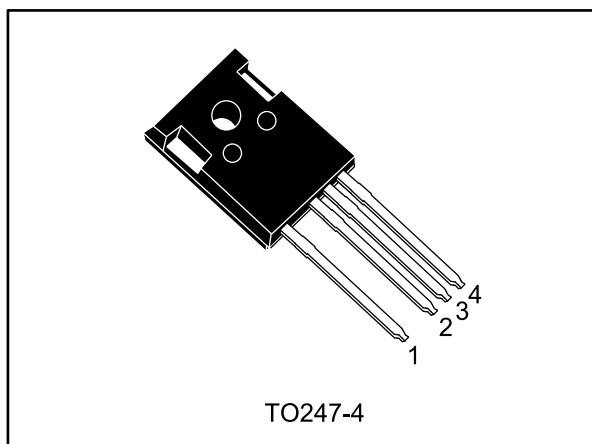
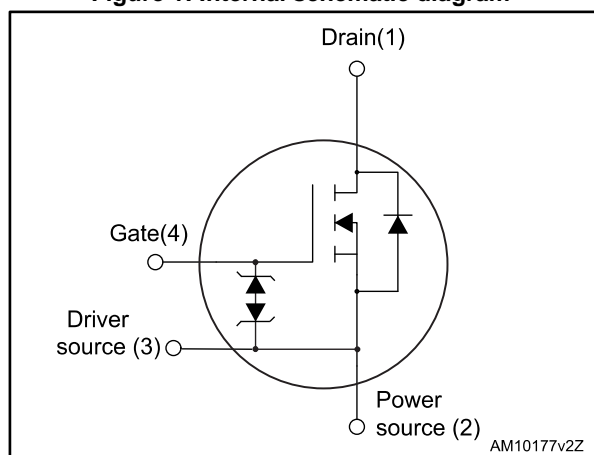


Figure 1: Internal schematic diagram



### Features

Order code	$V_{DS}$ @ $T_{Jmax.}$	$R_{DS(on)max.}$	$I_D$
STW48N60M2-4	650 V	0.07 $\Omega$	42 A

- Excellent switching performance thanks to the extra driving source pin
- Extremely low gate charge
- Excellent output capacitance ( $C_{oss}$ ) profile
- 100% avalanche tested
- Zener-protected

### Applications

- High efficiency switching applications:
  - Servers
  - PV inverters
  - Telecom infrastructure
  - Multi kW battery chargers

### Description

This device is an N-channel Power MOSFET developed using MDmesh™ M2 technology. Thanks to its strip layout and an improved vertical structure, the device exhibits low on-resistance and optimized switching characteristics, rendering it suitable for the most demanding high efficiency converters.

Table 1: Device summary

Order code	Marking	Package	Packing
STW48N60M2-4	48N60M2	TO247-4	Tube

---

## Contents

<b>1</b>	<b>Electrical ratings .....</b>	<b>3</b>
<b>2</b>	<b>Electrical characteristics .....</b>	<b>4</b>
	2.2 Electrical characteristics (curves) .....	6
<b>3</b>	<b>Test circuits .....</b>	<b>8</b>
<b>4</b>	<b>Package information .....</b>	<b>9</b>
	4.1 TO247-4 package information .....	9
<b>5</b>	<b>Revision history .....</b>	<b>11</b>

# 1 Electrical ratings

**Table 2: Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate- source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$	42	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	26	A
$I_{DM}^{(1)}$	Drain current (pulsed)	168	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ °C}$	300	W
$I_{AR}$	Max. current during repetitive or single pulse avalanche (pulse width limited by $T_{jmax.}$ )	7	A
$E_{AS}$	Single pulse avalanche energy (starting $T_j = 25\text{ °C}$ , $I_D = I_{AR}$ , $V_{DD} = 50\text{ V}$ )	1	J
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET $dv/dt$ ruggedness	50	V/ns
$T_{stg}$	Storage temperature range	- 55 to 150	°C
$T_j$	Operating junction temperature range		°C

**Notes:**

(1)Pulse width limited by safe operating area.

(2) $I_{SD} \leq 42\text{ A}$ ,  $di/dt = 400\text{ A}/\mu\text{s}$ ,  $V_{DS(peak)} < V_{(BR)DSS}$ ,  $V_{DD} = 400\text{ V}$

(3) $V_{DS} \leq 480\text{ V}$

**Table 3: Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max.	0.42	°C/W
$R_{thj-amb}$	Thermal resistance junction-ambient max.	50	°C/W

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 4: On /off-states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	600			V
$I_{DSS}$	Zero-gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 600\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 600\text{ V}$ , $T_C = 125\text{ °C}^{(1)}$			100	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			$\pm 10$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 21\text{ A}$		0.06	0.07	$\Omega$

**Notes:**

<sup>(1)</sup>Defined by design, not subject to production test.

**Table 5: Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	3060	-	pF
$C_{oss}$	Output capacitance		-	143	-	pF
$C_{rss}$	Reverse transfer capacitance		-	4.3	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent Output Capacitance	$V_{GS} = 0$ , $V_{DS} = 0\text{ to }480\text{ V}$	-	630	-	pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	4.6	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 480\text{ V}$ , $I_D = 42\text{ A}$ , $V_{GS} = 10\text{ V}$ See <a href="#">Figure 15: "Gate charge test circuit"</a>	-	70	-	nC
$Q_{gs}$	Gate-source charge		-	10.5	-	nC
$Q_{gd}$	Gate-drain charge		-	31	-	nC

**Notes:**

<sup>(1)</sup> $C_{oss\text{ eq.}}$  is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$ .

**Table 6: Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}$ , $I_D = 21\text{ A}$ , $R_G = 4.7\text{ }\Omega$ , $V_{GS} = 10\text{ V}$	-	18.5	-	ns
$t_r$	Rise time		-	17	-	ns
$t_{d(off)}$	Turn-off-delay time	See <a href="#">Figure 14: "Switching times test circuit for resistive load"</a> and <a href="#">Figure 19: "Switching time waveform"</a>	-	13	-	ns
$t_f$	Fall time		-	119	-	ns

Table 7: Source-drain diode

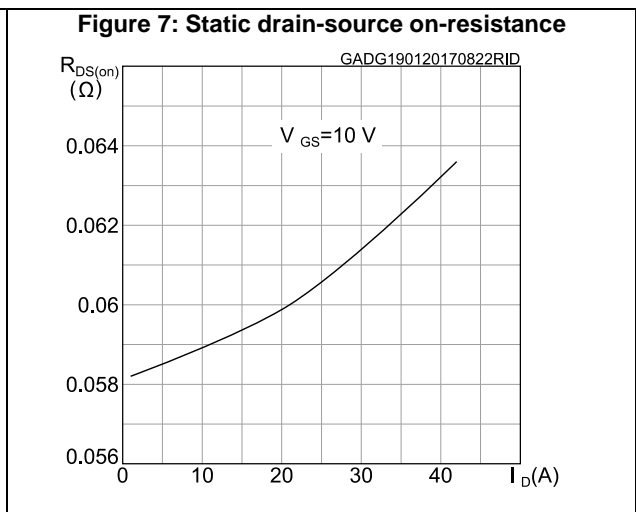
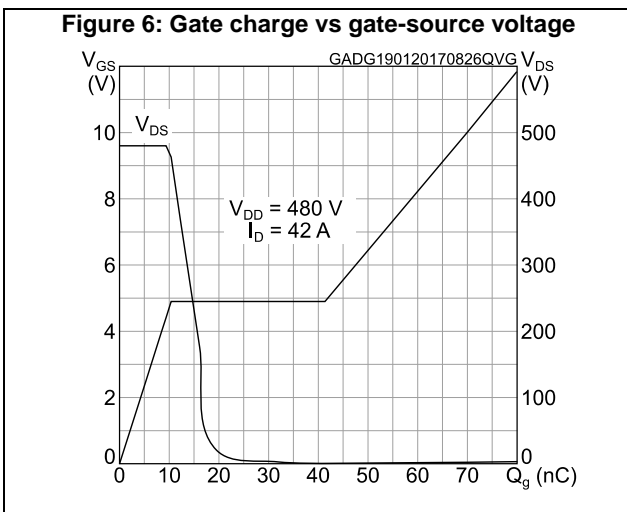
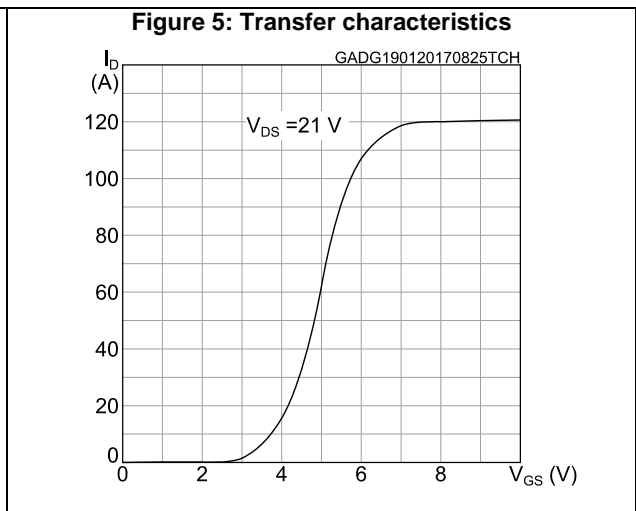
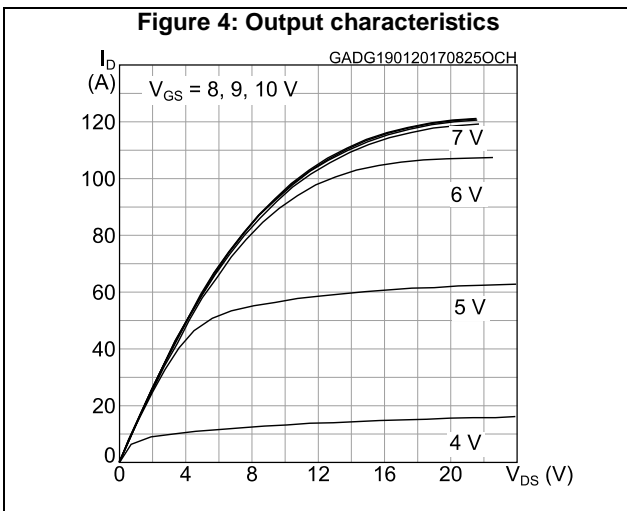
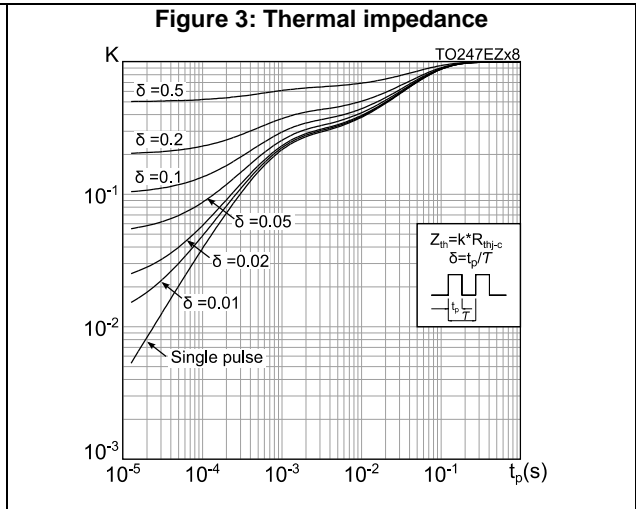
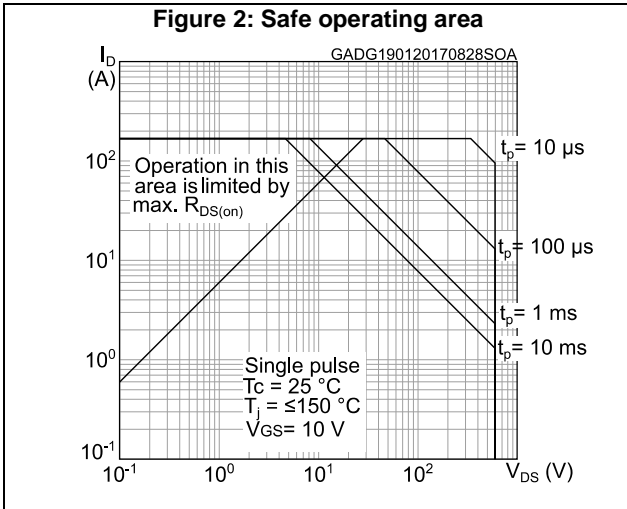
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		42	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		168	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 21 \text{ A}$ , $V_{GS} = 0$	-		1.6	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 42 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$	-	487		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60 \text{ V}$ See <i>Figure 16: "Test circuit for inductive load switching and diode recovery times"</i>	-	9.1		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	37.5		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 42 \text{ A}$ , $di/dt = 100 \text{ A}/\mu\text{s}$	-	605		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 60 \text{ V}$ , $T_j = 150 \text{ }^\circ\text{C}$ See <i>Figure 16: "Test circuit for inductive load switching and diode recovery times"</i>	-	12.5		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current		-	41.5		A

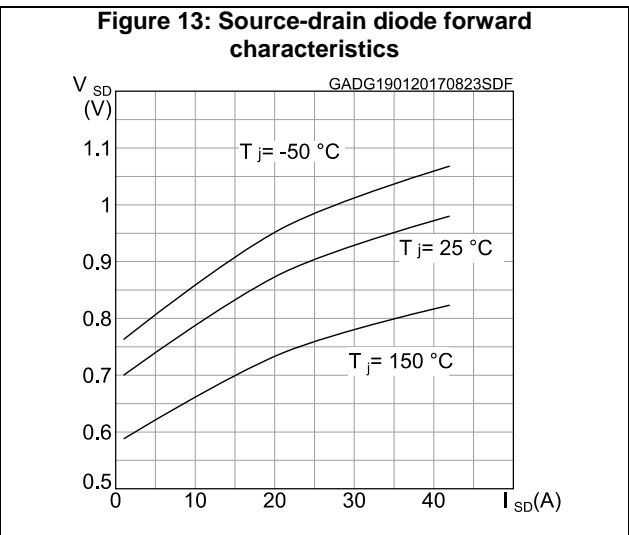
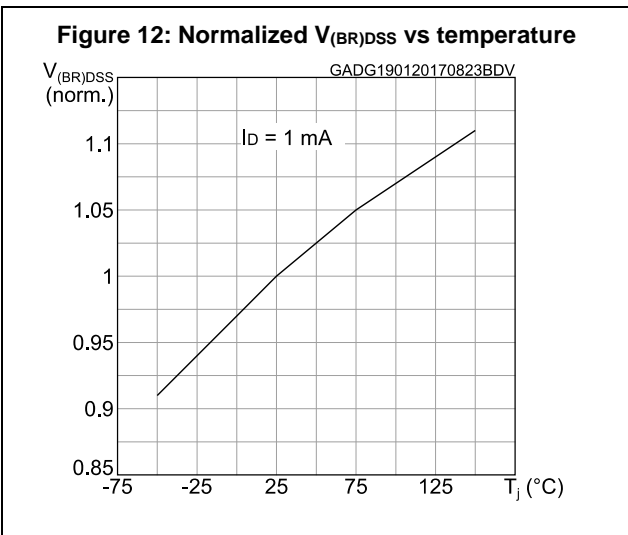
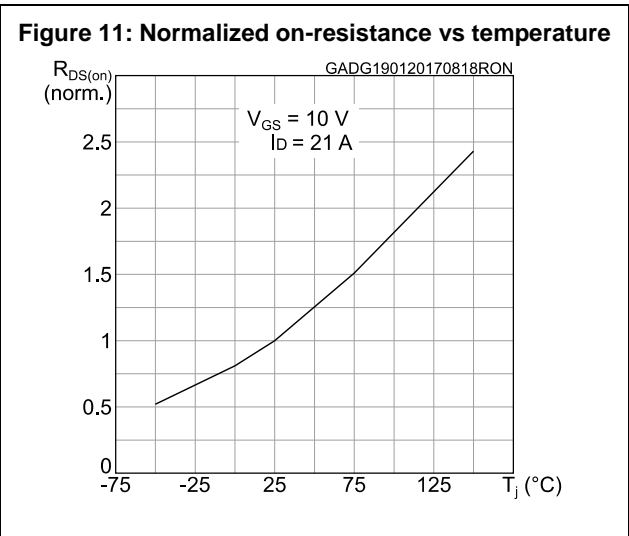
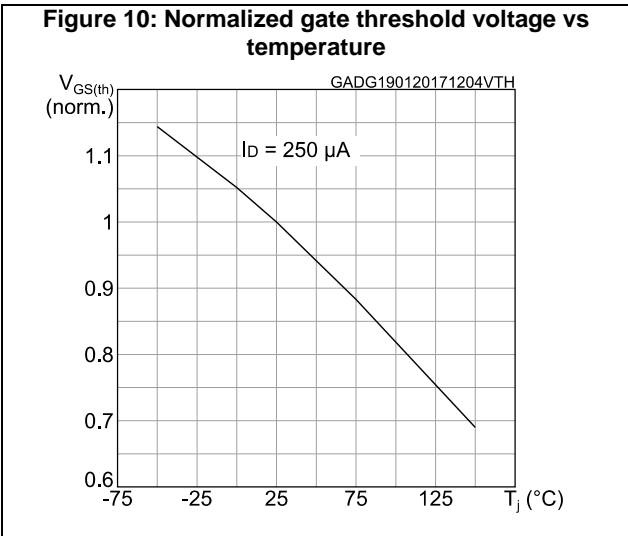
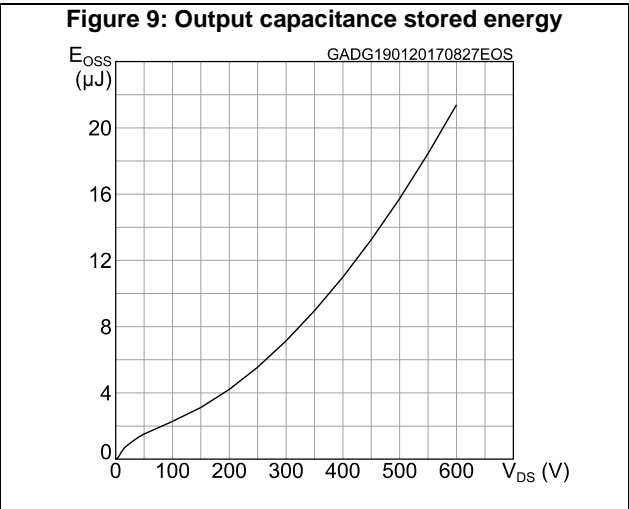
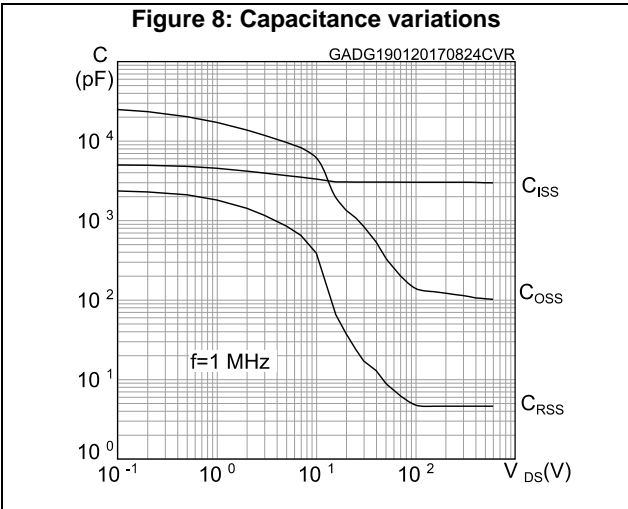
**Notes:**

(1)Pulse width limited by safe operating area.

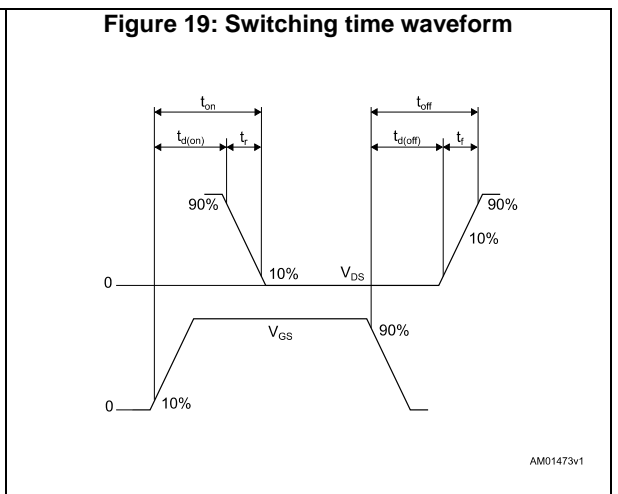
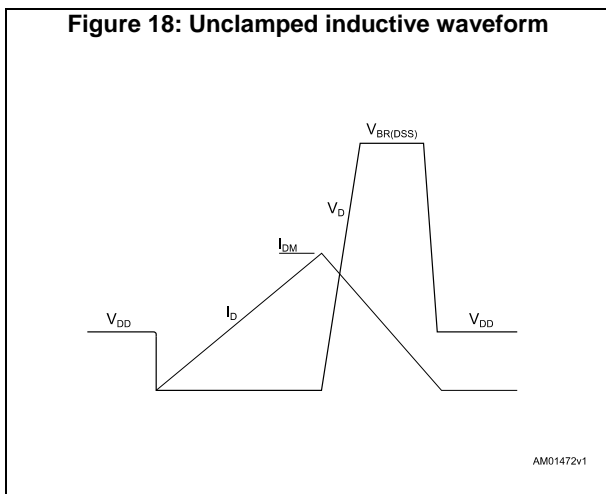
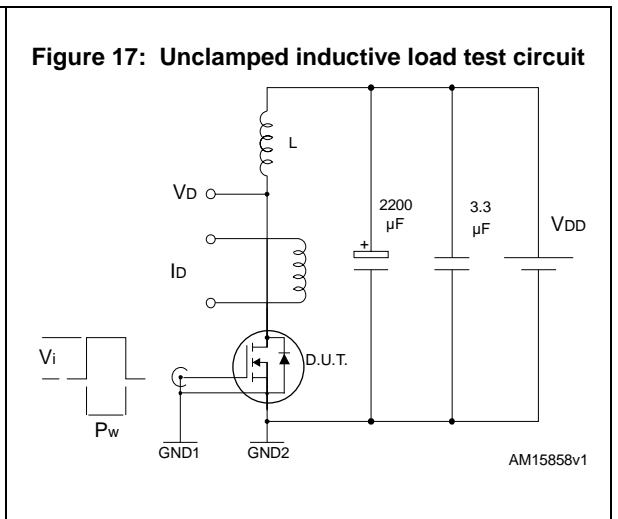
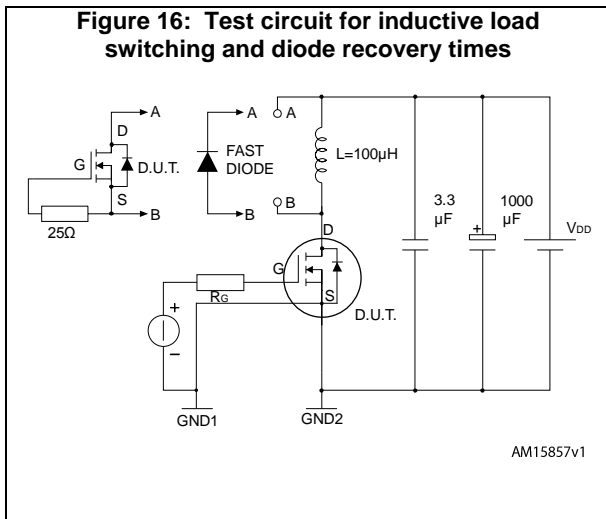
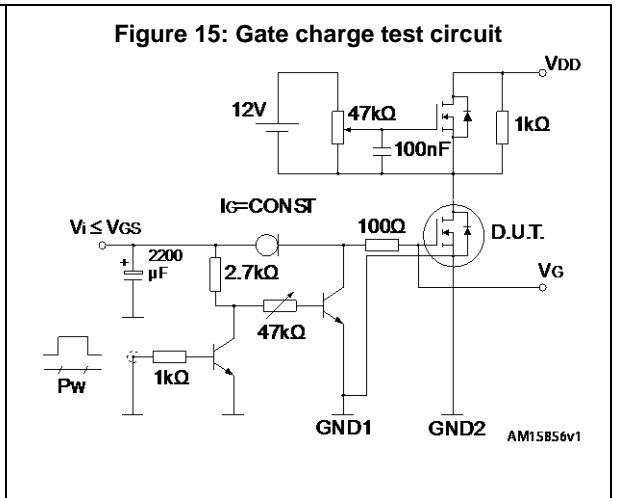
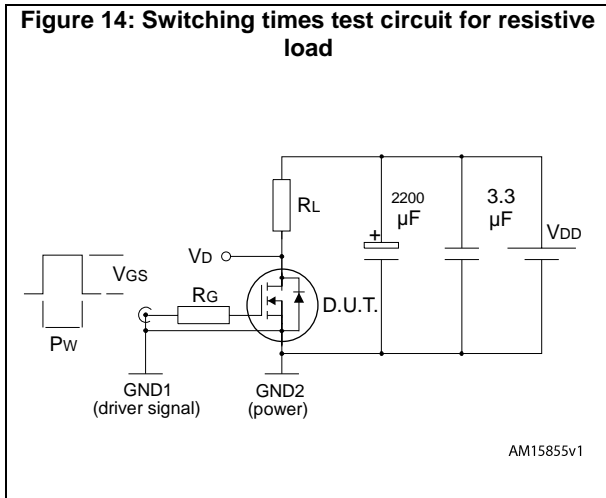
(2)Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%.

## 2.2 Electrical characteristics (curves)





### 3 Test circuits





## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK® is an ST trademark.

### 4.1 TO247-4 package information

Figure 20: TO247-4 package outline

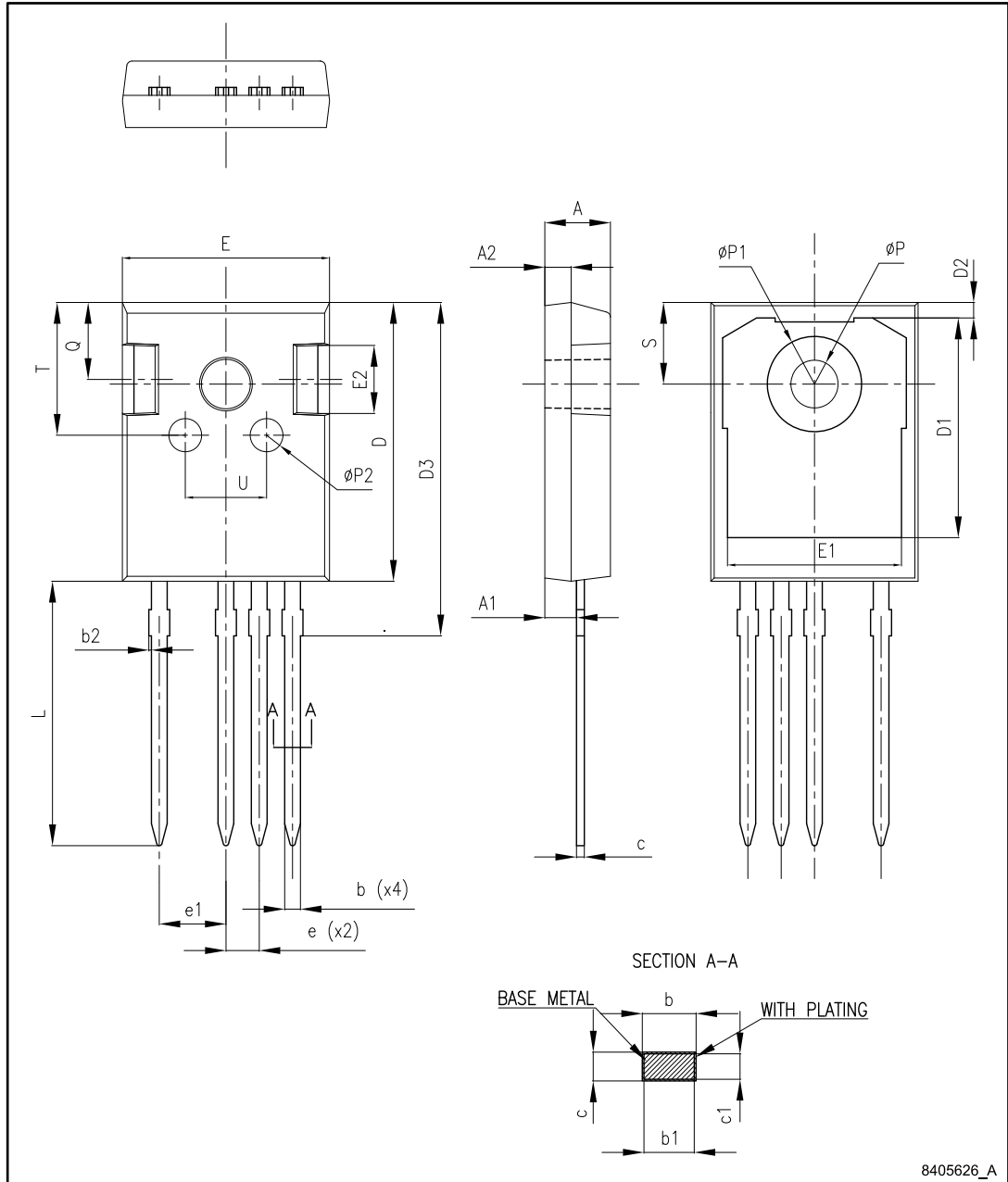


Table 8: TO247-4 mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
b	1.16		1.29
b1	1.15	1.20	1.25
b2	0		0.20
c	0.59		0.66
c1	0.58	0.60	0.62
D	20.90	21.00	21.10
D1	16.25	16.55	16.85
D2	1.05	1.20	1.35
D3	24.97	25.12	25.27
E	15.70	15.80	15.90
E1	13.10	13.30	13.50
E2	4.90	5.00	5.10
E3	2.40	2.50	2.60
e	2.44	2.54	2.64
e1	4.98	5.08	5.18
L	19.80	19.92	20.10
P	3.50	3.60	3.70
P1			7.40
P2	2.40	2.50	2.60
Q	5.60		6.00
S		6.15	
T	9.80		10.20
U	6.00		6.40

## 5 Revision history

**Table 9: Document revision history**

Date	Revision	Changes
25-Jul-2014	1	Initial release.
30-Jan-2015	2	Added section <i>Electrical characteristics (curves)</i> .
20-Jan-2017	3	Updated <a href="#">Table 2: "Absolute maximum ratings"</a> , <a href="#">Table 4: "On /off-states"</a> , <a href="#">Table 5: "Dynamic"</a> , <a href="#">Table 6: "Switching times"</a> and <a href="#">Table 7: "Source-drain diode"</a> . Updated <a href="#">Section 2.2: "Electrical characteristics (curves)"</a> .

**IMPORTANT NOTICE – PLEASE READ CAREFULLY**

STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, enhancements, modifications, and improvements to ST products and/or to this document at any time without notice. Purchasers should obtain the latest relevant information on ST products before placing orders. ST products are sold pursuant to ST's terms and conditions of sale in place at the time of order acknowledgement.

Purchasers are solely responsible for the choice, selection, and use of ST products and ST assumes no liability for application assistance or the design of Purchasers' products.

No license, express or implied, to any intellectual property right is granted by ST herein.

Resale of ST products with provisions different from the information set forth herein shall void any warranty granted by ST for such product.

ST and the ST logo are trademarks of ST. All other product or service names are the property of their respective owners.

Information in this document supersedes and replaces information previously supplied in any prior versions of this document.

© 2017 STMicroelectronics – All rights reserved